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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/539,997	06/17/2005	Arnold Forster	23315	1194
	7590 03/20/2007 KARL F ROSS	EXAMINER		
5676 RIVERDA		SOWARD, IDA M		
PO BOX 900 RIVERDALE (BRONX), NY 10471-0900			ART UNIT	PAPER NUMBER
			2822	
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SHORTENED STATUTOR	Y PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE	
3 MONTHS		03/20/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

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	Application No.	Applicant(s)					
Office Asticus Communication	10/539,997	FORSTER ET AL.					
Office Action Summary	Examiner	Art Unit					
	Ida M. Soward	2822					
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address					
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period was provided to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin vill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).					
Status							
1) Responsive to communication(s) filed on 17 Ju	ıne 2005.						
3) Since this application is in condition for allowar							
closed in accordance with the practice under E							
Disposition of Claims							
4) Claim(s) 1-12 is/are pending in the application.							
4a) Of the above claim(s) is/are withdrawn from consideration.							
5)⊠ Claim(s) <u>1-8 and 12</u> is/are allowed.							
6)⊠ Claim(s) <u>9 and 11</u> is/are rejected.							
7)⊠ Claim(s) <u>1 and 10</u> is/are objected to.	7)⊠ Claim(s) <u>1 and 10</u> is/are objected to.						
8) Claim(s) are subject to restriction and/o	r election requirement.						
Application Papers							
9)⊠ The specification is objected to by the Examine	r.						
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.							
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).							
Replacement drawing sheet(s) including the correct	ion is required if the drawing(s) is ob	jected to. See 37 CFR 1.121(d).					
11)☐ The oath or declaration is objected to by the Ex	aminer. Note the attached Office	Action or form PTO-152.					
Priority under 35 U.S.C. § 119							
12)⊠ Acknowledgment is made of a claim for foreign a)⊠ All b)□ Some * c)□ None of:	priority under 35 U.S.C. § 119(a)-(d) or (f).					
1. Certified copies of the priority documents	s have been received.						
2. Certified copies of the priority documents have been received in Application No							
Copies of the certified copies of the prior	rity documents have been receive	ed in this National Stage					
application from the International Bureau (PCT Rule 17.2(a)).							
* See the attached detailed Office action for a list of the certified copies not received.							
•							
Attachment(s)	n.□	(DTO 442)					
1) X Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) Ll Interview Summary Paper No(s)/Mail D						
3) Information Disclosure Statement(s) (PTO/SB/08)	5) 🔲 Notice of Informal F						
Paper No(s)/Mail Date <u>06/17/2005</u> . 6) Other:							

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DETAILED ACTION

This Office Action is in response to the preliminary amendment filed June 17, 2005.

Priority

Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Specification

The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim Objections

Claim 1 is objected to because of the following informalities: "firstly" should have been <u>first</u> in line 5. Appropriate correction is required.

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 11 is recites the limitation "the second undoped GaAs layer" in lines 17-

18. There is insufficient antecedent basis for this limitation in the claim.

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Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 9 is rejected under 35 U.S.C. 103(a) as being unpatentable over Twynam (6,111,265).

In regard to claim 9, Twynam teaches a method of making a layer sequence or structure with the steps: a first highly doped GaAs layer 55 disposed on a substrate (not shown), on the first highly doped GaAs layer 55 an underdoped GaAs layer 54 is arranged, on the underdoped GaAs layer 54 a graded AlGaAs layer 52 is disposed (Figure 5A, column 2, lines 33-55).

However, Twynam fails to teach the underdoped GaAs layer being epitaxied at an appropriate temperature.

Epitaxially grown GaAs layers at appropriate temperatures are well known in the art of compound semiconductor devices.

Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the method as taught by Twynam to epitaxy the underdoped GaAs layer at the appropriate temperature to have improved operation efficiency (column 4, lines 31-36).

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Allowable Subject Matter

Claims 1-8 and 12 are allowed.

The following is a statement of reasons for the indication of allowable subject matter: The prior art of record does not disclose, make obvious, or otherwise suggest the structure of the applicant's together with the other limitations of the independent claims, such as:

In claim 1, "a graded layer (5) of AlGaAs on the firstly highly doped layer (3) whereby the aluminum concentration of this layer diminishes, starting from the boundary surface with the first highly doped layer, in the direction of the opposite boundary surface of the AlGaAs layer (5); and a second highly doped n*-layer (7), characterized in that on at least one boundary layer of the AlGaAs layer (5) an undoped intermediate layer (4,6) juxtaposed with the respective highly doped layer (3,7) is provided"; and

In claim 12, "a second highly doped layer, characterized in that on at least one boundary surface of the graded layer an undoped intermediate layer is arranged and juxtaposed with one of the highly doped layers".

The dependent claims being further limiting and definite are also allowable.

Claim 10 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

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Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

The following patents are cited to further show the state of the art with respect to GaAs layered structures:

Awao (4914,489)

Battersby (5,675,157)

Battersby et al. (5,250,815)

Battersby et al. (5,258,624)

Davey et al. (4,188,710)

Dully (3,981,073)

Kimura et al. (US 6,686,647 B2)

Smith (5,151,758)

Yariv et al. (4,212,020).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ida M. Soward whose telephone number is 571-272-1845. The examiner can normally be reached on Monday - Thursday 6:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra V. Smith can be reached on 571-272-2429. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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IMS

March 15, 2007

IDA M. SOWARD

PRIMARY EXAMINER